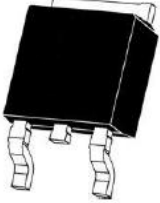
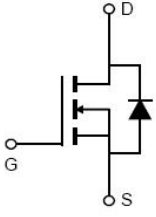


QIAOXIN N-Channel Super Trench II Power MOSFET

<p>Description</p> <p>The series of devices uses Super Trench II technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.</p> <p>Application</p> <ul style="list-style-type: none"> ● DC/DC Converter ● Ideal for high-frequency switching and synchronous rectification 	<p>General Features</p> <ul style="list-style-type: none"> ● $V_{DS} = 120V, I_D = 65A$ $R_{DS(ON)} = 8.7m\Omega$, typical @ $V_{GS} = 10V$ ● Excellent gate charge x $R_{DS(on)}$ product(FOM) ● Very low on-resistance $R_{DS(on)}$ ● 175 °C operating temperature ● Pb-free lead plating
<p>TO-252</p> 	 <p>Schematic Diagram</p>

Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRR10N12K		TO-252-2L

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	65	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	46	A
Pulsed Drain Current	I_{DM}	260	A
Maximum Power Dissipation	P_D	120	W
Derating factor		0.8	W/°C
Single pulse avalanche energy ^(Note 4)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =35A	-	8.7	10.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =35A		60	-	S
Dynamic Characteristics (Note 3)						
Input Capacitance	C _{iss}	V _{DS} =60V, V _{GS} =0V, F=1.0MHz	-	3050	-	pF
Output Capacitance	C _{oss}		-	280	-	pF
Reverse Transfer Capacitance	C _{rss}		-	22	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =60V, I _D =35A V _{GS} =10V, R _G =1.6Ω	-	15	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q _g	V _{DS} =60V, I _D =35A, V _{GS} =10V	-	53	-	nC
Gate-Source Charge	Q _{gs}		-	20	-	nC
Gate-Drain Charge	Q _{gd}		-	12.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V, I _S =35A	-	-	1.2	V
Diode Forward Current	I _S		-	-	65	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 35A	-	60	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note 3)	-	106	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production
4. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.25mH, R_G=25Ω
5. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating

Typical Electrical and Thermal Characteristics

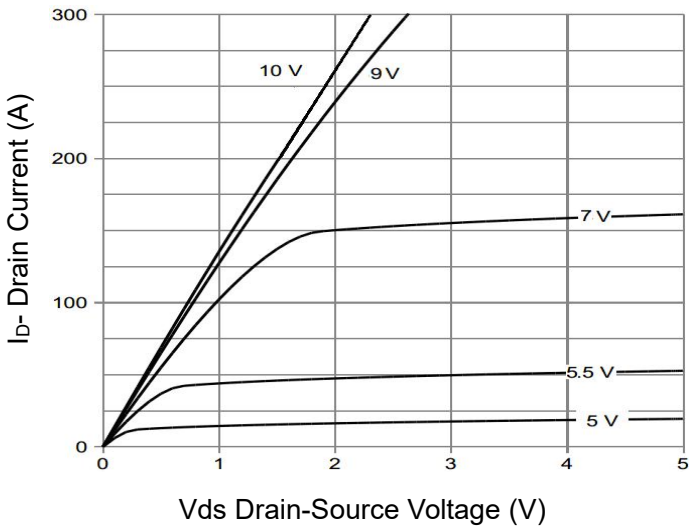


Figure 1 Output Characteristics

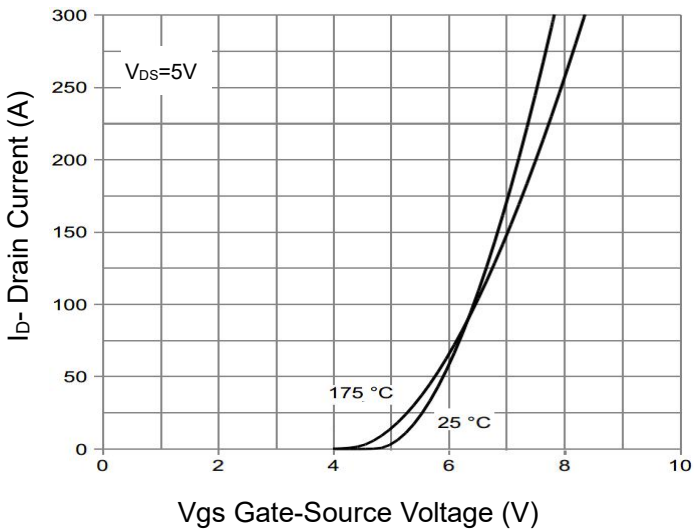


Figure 2 Transfer Characteristics

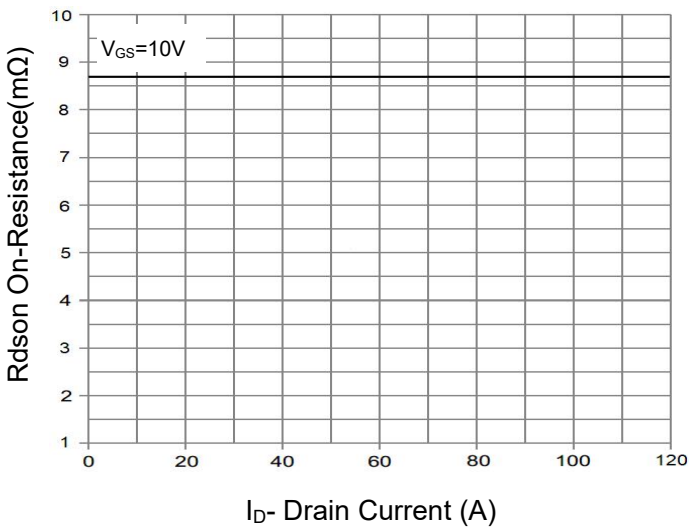


Figure 3 Rdson- Drain Current

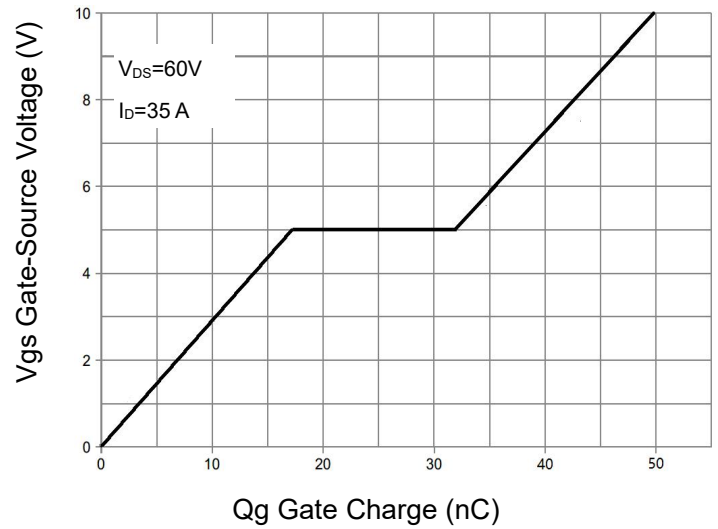


Figure 4 Gate Charge

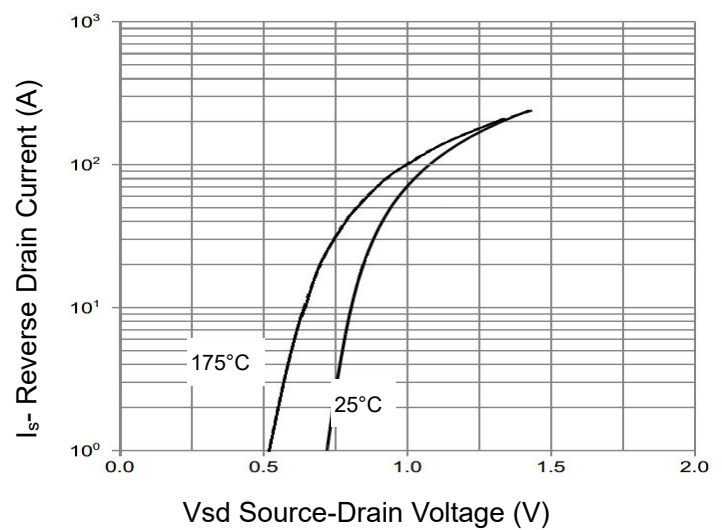


Figure 5 Source- Drain Diode Forward

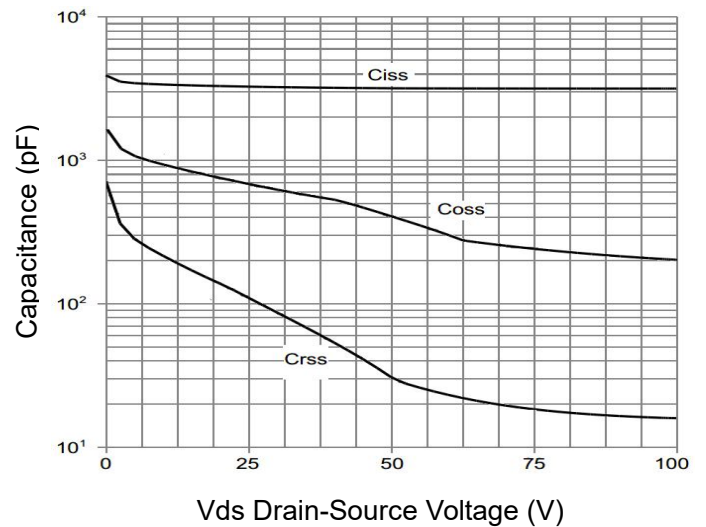
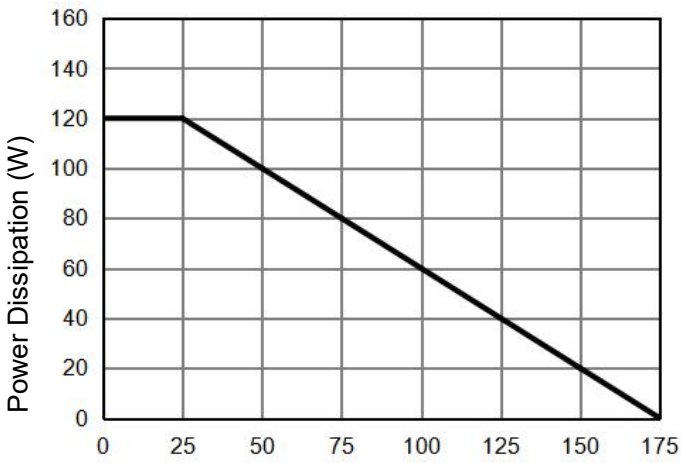
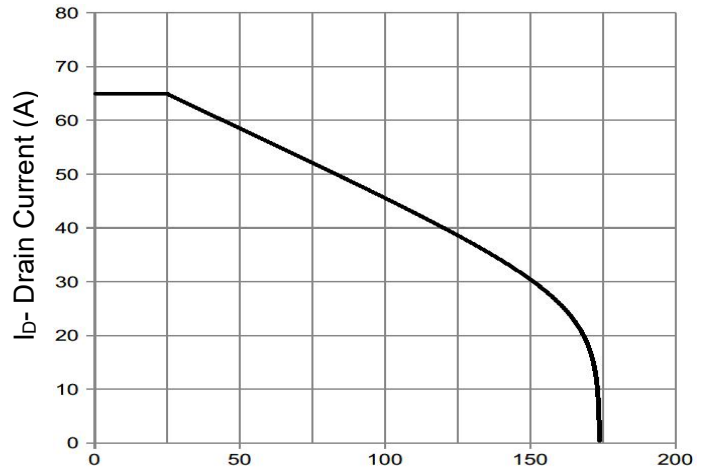


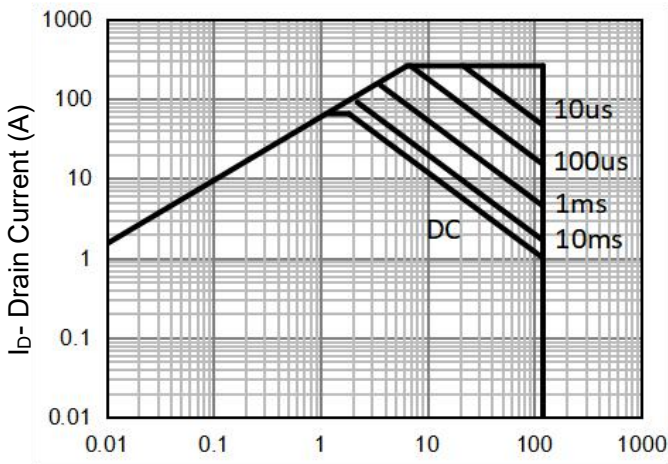
Figure 6 Capacitance vs Vds



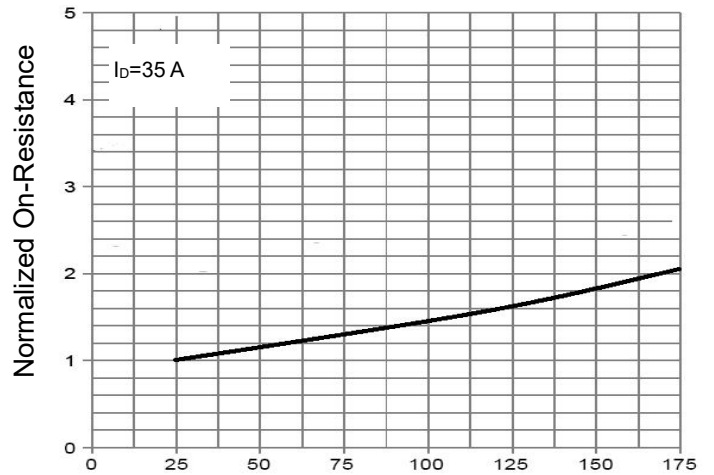
T_A -Junction Temperature ($^{\circ}C$)
Figure 7 Power De-rating



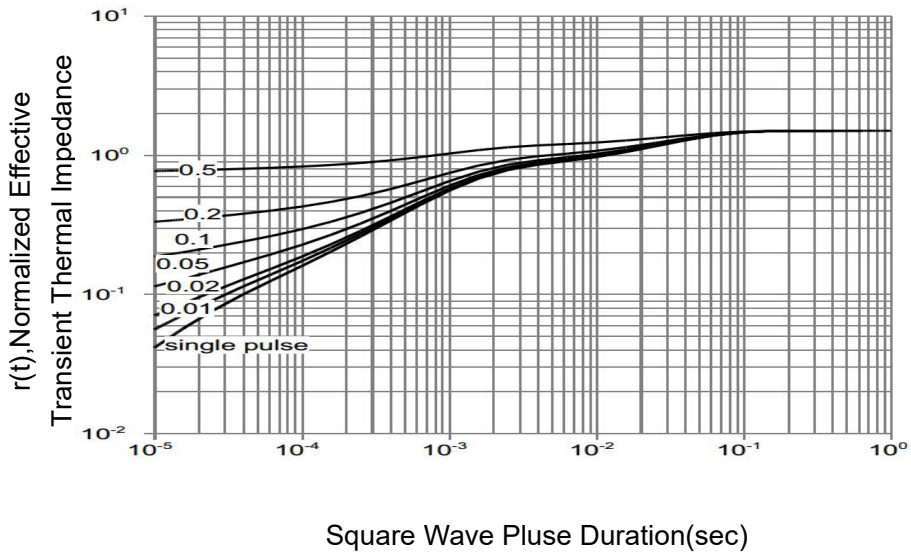
T_A -Junction Temperature ($^{\circ}C$)
Figure 9 Current De-rating



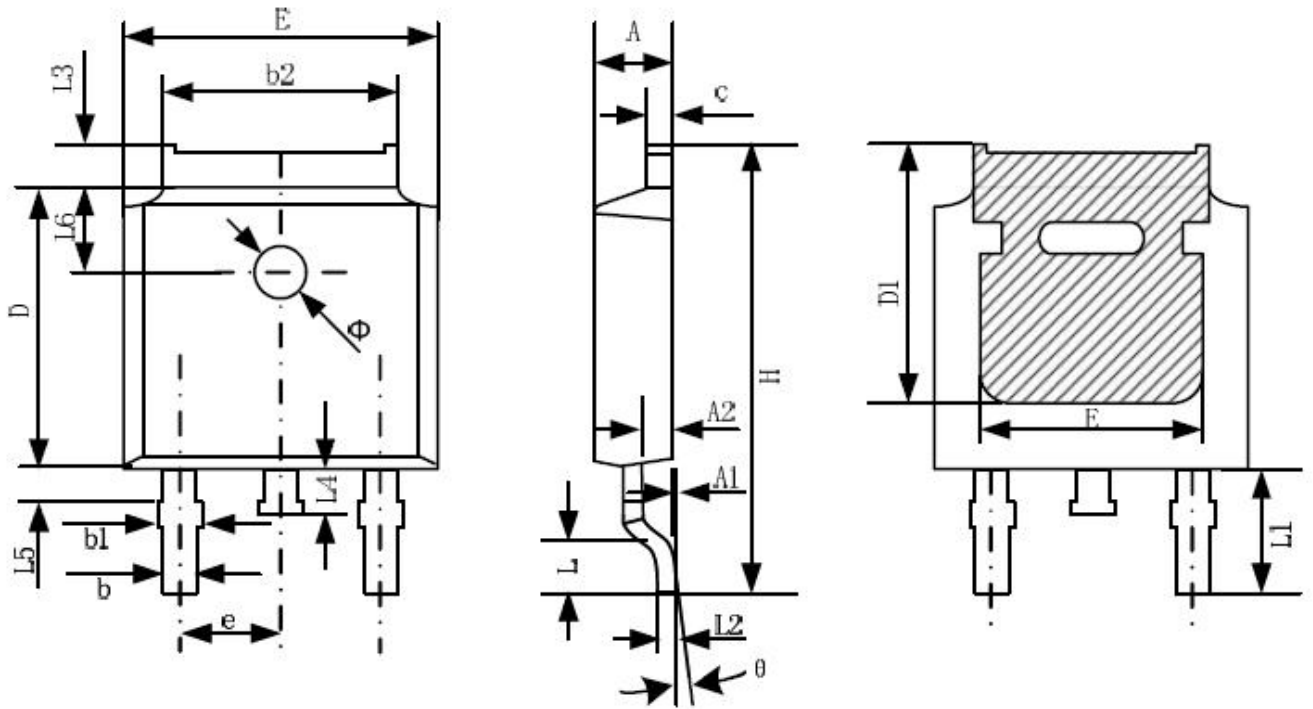
V_{ds} Drain-Source Voltage (V)
Figure 8 Safe Operation Area (Note 5)



T_J -Junction Temperature ($^{\circ}C$)
Figure 10 R_{dson} -Junction Temperature



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.38	0.087	0.094
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.72	0.85	0.028	0.033
b1	0.72	0.90	0.028	0.035
b2	5.13	5.46	0.202	0.215
c	0.47	0.60	0.019	0.024
D	6.00	6.20	0.236	0.244
D1	5.25	--	0.207	--
E	6.50	6.70	0.256	0.264
E1	4.70	--	0.185	--
e	2.19	2.39	0.086	0.094
H	9.80	10.40	0.386	0.409
L	1.40	1.70	0.055	0.067
L1	2.90 REF		0.114 REF	
L2	0.508 BSC		0.020 BSC	
L3	0.90	1.25	0.035	0.049
L4	0.60	1.00	0.024	0.039
L5	0.15	0.75	0.006	0.030
L6	1.80 REF		0.071 REF	
Φ	1.20	1.40	0.047	0.055
θ	0°	8°	0°	8°

Attention

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